

**ATTACHMENT: Version With Markings Showing Changes Made**

Please amend Claims 21 and 34 as follows:

21. (Amended) A semiconductor structure comprising at least one metal silicate dielectric material that is formed on a silicon oxide layer, said silicon oxide layer being formed on a Si-containing substrate.

34. ( Twice Amended) A capacitor comprising at least one metal silicate dielectric material sandwiched between the same or different electrode materials, wherein said at least one metal silicate is obtained by forming a metal oxide layer on a silicon-containing material and heating said metal oxide layer in the presence of an oxidizing agent under conditions so as to convert said metal oxide layer into said metal silicate while simultaneously oxidizing a portion of the silicon-containing material underlying the metal silicate.